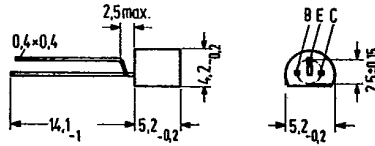


**NPN Silicon RF Transistor**

SIEMENS AKTIENGESELLSCHAFT : 04509

BF 505 is an NPN silicon planar RF transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is particularly intended for use in VHF amplifiers in common emitter configuration, VHF mixers and VHF/UHF oscillators.

Type	Ordering code
BF 505	Q62702-F573



Approx. weight 0.25 g

Dimensions in mm

**Maximum ratings ( $T_{amb} = 25^{\circ}\text{C}$ )**

Collector-emitter voltage  
Collector-base voltage  
Emitter-base voltage  
Collector current  
Collector peak current  
Base current  
Junction temperature  
Storage temperature range  
Total power dissipation

$V_{CEO}$	25	V
$V_{CBO}$	30	V
$V_{EBO}$	3	V
$I_C$	20	mA
$I_{CM}$	50	mA
$I_B$	5	mA
$T_j$	150	$^{\circ}\text{C}$
$T_{stg}$	-55 to +150	$^{\circ}\text{C}$
$P_{tot}$	500	mW

**Thermal resistance**

Junction to ambient air

$R_{thJA}$	$\leq 250$	K/W
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## NPN Silicon RF Transistor

BF 505

SIEMENS AKTIENGESELLSCHAFT

Static characteristics ( $T_{amb} = 25^{\circ}\text{C}$ )

Collector cutoff current

( $V_{CBO} = 25\text{ V}$ ) $I_{CBO} \leq 100$  nA

Collector-emitter breakdown voltage

( $I_C = 1\text{ mA}$ ) $V_{(BR)CEO} \geq 25$  V

Collector-base breakdown voltage

( $I_C = 10\text{ }\mu\text{A}$ ) $V_{(BR)CBO} \geq 30$  V

Emitter-base breakdown voltage

( $I_E = 10\text{ }\mu\text{A}$ ) $V_{(BR)EBO} \geq 3$  V

DC current gain

( $I_C = 1\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ) $h_{FE} \geq 30$  -( $I_C = 5\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ) $h_{FE} \geq 40$  -

Base-emitter voltage

( $I_C = 5\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ) $V_{BE} \leq 0.95$  V

Collector-emitter saturation voltage

( $I_C = 5\text{ mA}$ ;  $I_B = 0.5\text{ mA}$ ) $V_{CEsat} \leq 0.6$  VDynamic characteristics ( $T_{amb} = 25^{\circ}\text{C}$ )

Transition frequency

( $I_C = 5\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ;  $f = 100\text{ MHz}$ ) $f_T \geq 750$  MHz

Noise figure

( $I_C = 3\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ;  $f = 200\text{ MHz}$ ;  $R_g = 60\text{ }\Omega$ ) $NF = 3$  dB

Collector-base capacitance

( $f = 1\text{ MHz}$ ;  $V_{CB} = 10\text{ V}$ ;  $V_{BE} = 0\text{ V}$ )<sup>1)</sup> $C_{CB} \leq 0.5$  pF

Collector-emitter capacitance

( $f = 1\text{ MHz}$ ;  $V_{CB} = 10\text{ V}$ ;  $V_{BE} = 0\text{ V}$ )<sup>1)</sup> $C_{CE} \leq 1.1$  pF

1) Third terminal at screening potential



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